



**CHENMKO ENTERPRISE CO., LTD**

*Lead free devices*

**SURFACE MOUNT  
NPN Switching Transistor**

**VOLTAGE 40 Volts CURRENT 0.2 Ampere**

**CH3904PT**

**APPLICATION**

- \* Telephony and professional communication equipment.
- \* Other switching applications.

**FEATURE**

- \* Small surface mounting type. (SOT-23)
- \* Low current (Max.=200mA).
- \* Suitable for high packing density.
- \* Low voltage (Max.=40V).
- \* High saturation current capability.
- \* Voltage controlled small signal switch.

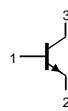
**CONSTRUCTION**

- \* NPN Switching Transistor

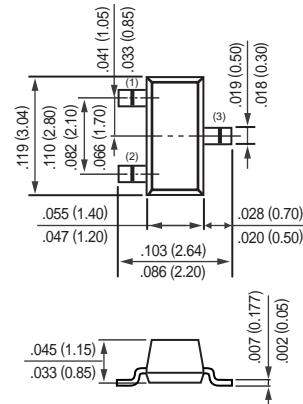
**MARKING**

- \* s1A

**CIRCUIT**



**SOT-23**



Dimensions in inches and (millimeters)

**SOT-23**

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	—	60	V
$V_{CEO}$	collector-emitter voltage	open base	—	40	V
$V_{EBO}$	emitter-base voltage	open collector	—	6	V
$I_C$	collector current DC		—	200	mA
$I_{CM}$	peak collector current		—	200	mA
$I_{BM}$	peak base current		—	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25^\circ\text{C}$ ; note 1	—	330	mW
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	junction temperature		—	150	°C
$T_{amb}$	operating ambient temperature		-65	+150	°C

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

2004-4

## RATING CHARACTERISTIC CURVES ( CH3904PT )

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

**Note**

- Transistor mounted on an FR4 printed-circuit board.

### CHARACTERISTICS

$T_{amb} = 25^\circ C$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 30 V$	—	50	nA
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 6 V$	—	50	nA
$h_{FE}$	DC current gain	$V_{CE} = 1 V$ ; note 1 $I_C = 0.1 mA$ $I_C = 1 mA$ $I_C = 10 mA$ $I_C = 50 mA$ $I_C = 100 mA$	60 80 100 60 30	— — 300 — —	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10 mA; I_B = 1 mA$	—	200	mV
		$I_C = 50 mA; I_B = 5 mA$	—	300	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10 mA; I_B = 1 mA$	650	850	mV
		$I_C = 50 mA; I_B = 5 mA$	—	950	mV
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = 5 V; f = 1 MHz$	—	4	pF
$C_e$	emitter capacitance	$I_C = i_c = 0; V_{BE} = 500 mV; f = 1 MHz$	—	8	pF
$f_T$	transition frequency	$I_C = 10 mA; V_{CE} = 20 V; f = 100 MHz$	300	—	MHz
$F$	noise figure	$I_C = 100 \mu A; V_{CE} = 5 V; R_S = 1 k\Omega; f = 10 Hz to 15.7 kHz$	—	5	dB

### Switching times (between 10% and 90% levels);

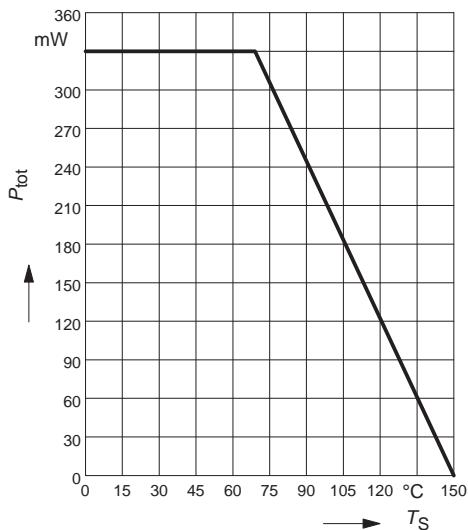
$t_{on}$	turn-on time	$I_{Con} = 10 mA; I_{Bon} = 1 mA; I_{Boff} = -1 mA$	—	65	ns
$t_d$	delay time		—	35	ns
$t_r$	rise time		—	35	ns
$t_{off}$	turn-off time		—	240	ns
$t_s$	storage time		—	200	ns
$t_f$	fall time		—	50	ns

**Note**

- Pulse test:  $t_p \leq 300 \mu s; \delta \leq 0.02$ .

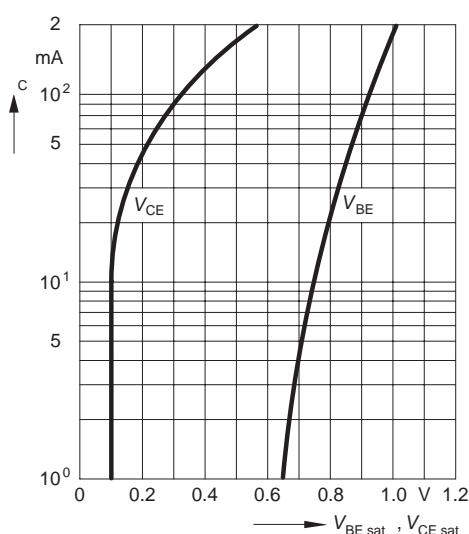
## RATING CHARACTERISTIC CURVES ( CH3904PT )

**Total power dissipation**  $P_{\text{tot}} = f(T_S)$



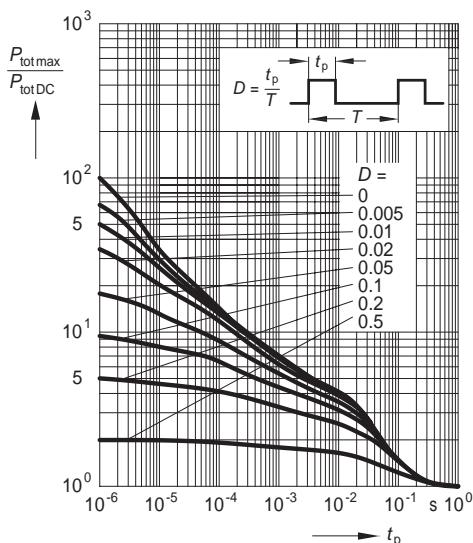
**Saturation voltage**  $I_C = f(V_{BE\text{sat}}, V_{CE\text{sat}})$

$h_{FE} = 10$



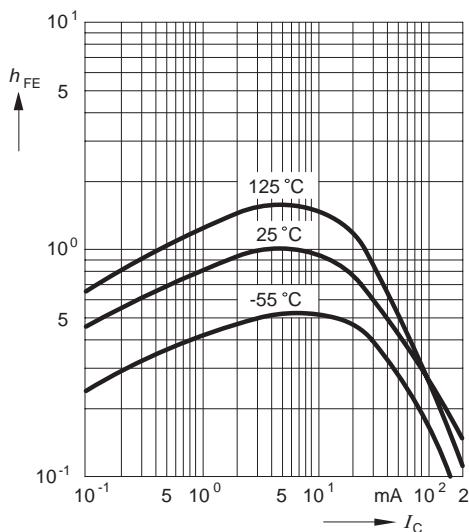
**Permissible pulse load**

$P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$

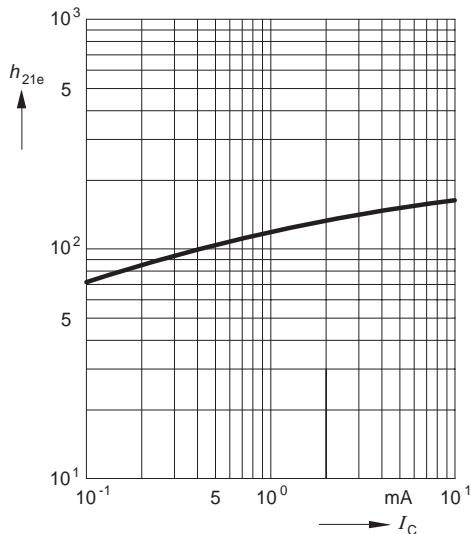
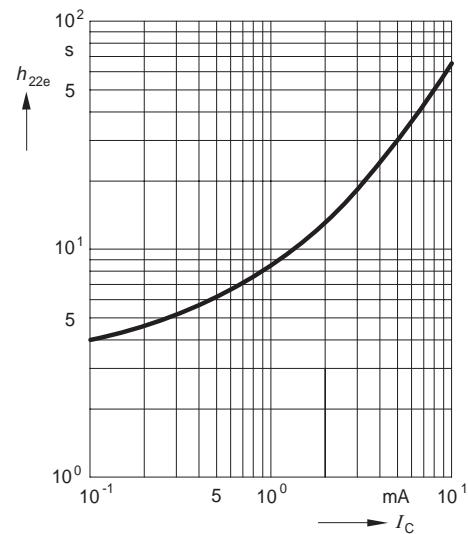
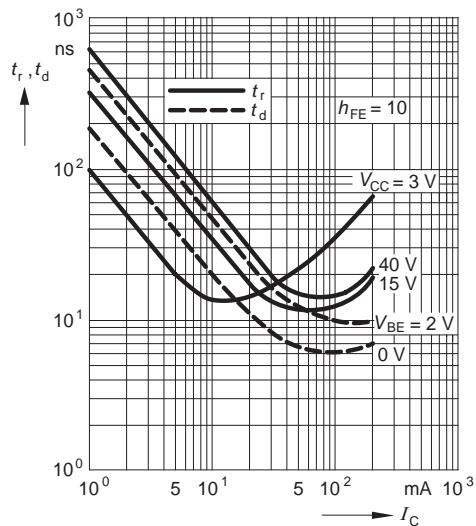
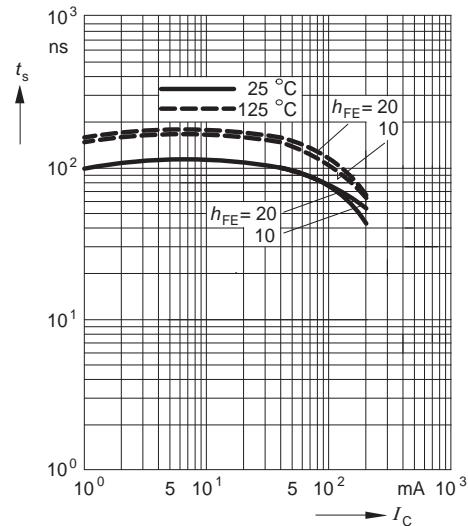


**DC current gain**  $h_{FE} = f(I_C)$

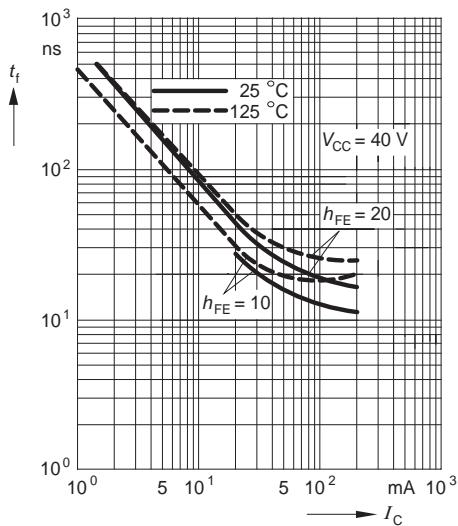
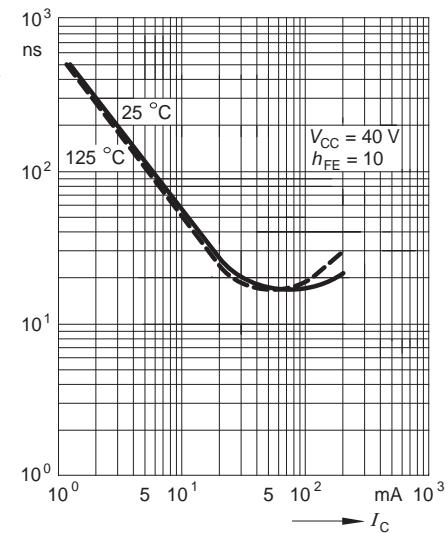
$V_{CE} = 10V$ , normalized



## RATING CHARACTERISTIC CURVES ( CH3904PT )

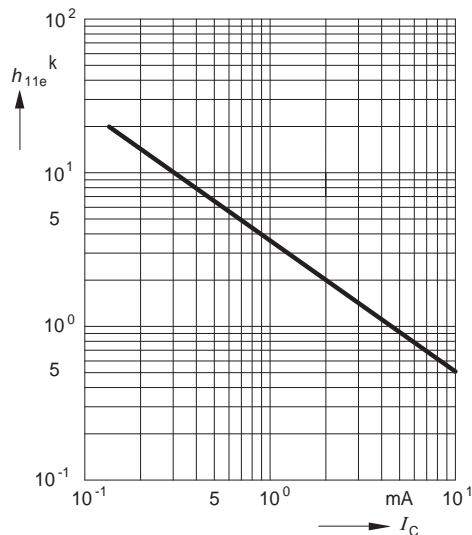
**Short-circuit forward current**
**transfer ratio**  $h_{21e} = f(I_C)$ 
 $V_{CE} = 10V, f = 1MHz$ 

**Open-circuit output admittance**
 **$h_{22e} = f(I_C)$** 
 $V_{CE} = 10V, f = 1MHz$ 

**Delay time**  $t_d = f(I_C)$ 
**Rise time**  $t_r = f(I_C)$ 

**Storage time**  $t_{stg} = f(I_C)$ 


## RATING CHARACTERISTIC CURVES ( CH3904PT )

**Fall time  $t_f = f(I_C)$** **Rise time  $t_r = f(I_C)$** **Input impedance**

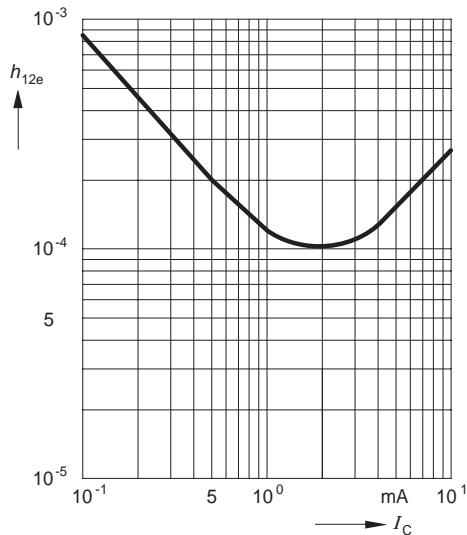
$$h_{11e} = f(I_C)$$

$V_{CE} = 10$  V,  $f = 1$  kHz

**Open-circuit reverse voltage**

$$\text{transfer ratio } h_{12e} = f(I_C)$$

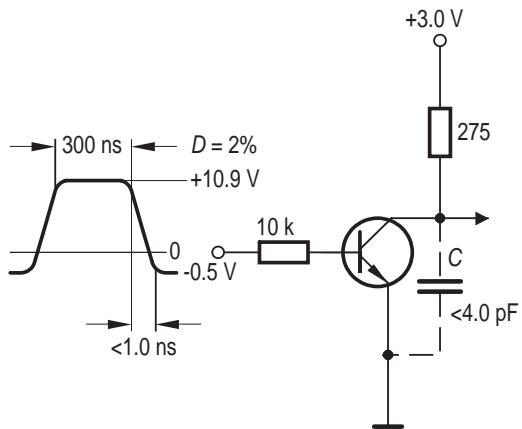
$V_{CE} = 10$  V,  $f = 1$  kHz



## RATING CHARACTERISTIC CURVES ( CH3904PT )

### Test circuits

#### Delay and rise time



#### Storage and fall time

